## P-Channel 200-V (D-S) MOSFET

#### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

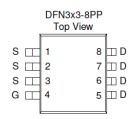
### **Typical Applications:**

- PoE Power Sourcing Equipment
- PoE Powered Devices
- Telecom DC/DC converters

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)	
-200	900 @ V <sub>GS</sub> = -10V	-1.6	
	1000 @ V <sub>GS</sub> = -5.5V	-1.5	







ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Limit	Units				
Drain-Source Voltage			-200	V			
Gate-Source Voltage	$V_{GS}$	±20	V				
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =25°C	I L	-1.6				
Continuous Drain Current	T <sub>A</sub> =70°C	I <sub>D</sub>	-1.2	Α			
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	-7					
Continuous Source Current (Diode Conduction) a		I <sub>S</sub>	-3.8	Α			
Power Dissipation <sup>a</sup>	T <sub>A</sub> =25°C	$P_{D}$	3.5	W			
Prower Dissipation	T <sub>A</sub> =70°C	] 'D	2	V V			
Operating Junction and Storage Temperature Range		$T_J$ , $T_{stg}$	-55 to 150	°C			

THERMAL RESISTANCE RATINGS							
Parameter			Maximum	Units			
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	$R_{\theta JA}$	35	°C/W			
Maximum Junction-to-Ambient	Steady State	IXOJA	81	C/VV			

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#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

#### **Electrical Characteristics**

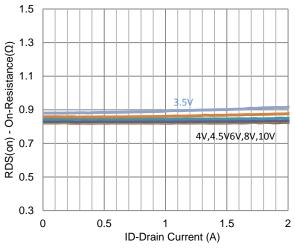
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±10	uA	
Zero Gate Voltage Drain Current	lane	$V_{DS} = -160 \text{ V}, V_{GS} = 0 \text{ V}$			-1 uA		
Zero Gate Voltage Brain Current	I <sub>DSS</sub>	$V_{DS} = -160 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-10	uA	
On-State Drain Current	I <sub>D(on)</sub>	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-1.5			Α	
Drain-Source On-Resistance	r	$V_{GS} = -10 \text{ V}, I_{D} = -1.4 \text{ A}$			900 mΩ		
Dialii-Source Ori-Nesistance	r <sub>DS(on)</sub>	$V_{GS} = -5.5 \text{ V}, I_D = -1.3 \text{ A}$			1000	11122	
Forward Transconductance	g <sub>fs</sub>	$V_{DS} = -15 \text{ V}, I_{D} = -1.4 \text{ A}$		10		S	
Diode Forward Voltage	$V_{SD}$	$I_S = -1.9 \text{ A}, V_{GS} = 0 \text{ V}$		0.87		V	
		Dynamic					
Total Gate Charge	$Q_g$	$V_{DS} = -100 \text{ V}, V_{GS} = -5.5 \text{ V},$		10.6			
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -100 \text{ V}, V_{GS} = -5.5 \text{ V},$ $I_{D} = -1.4 \text{ A}$		3.2		nC	
Gate-Drain Charge	$Q_{gd}$	1D = 1.4 V		4.2			
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DD} = -100 \text{ V}, R_L = 71.4 \Omega$		4			
Rise Time	t <sub>r</sub>	$V_{DD} = -100 \text{ V}, K_L = 71.4 \Omega,$ $I_D = -1.4 \text{ A}, V_{GEN} = -10 \text{ V},$		11		ne	
Turn-Off Delay Time	t <sub>d(off)</sub>	$R_{GEN} = 6 \Omega$		59		ns	
Fall Time	t <sub>f</sub>	INGEN - U 12		69			
Input Capacitance	C <sub>iss</sub>			1005			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		93		pF	
Reverse Transfer Capacitance	$C_{rss}$			67			

#### Notes

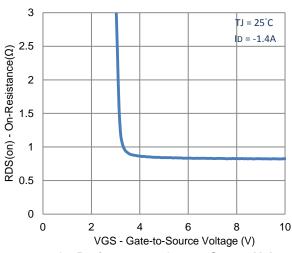
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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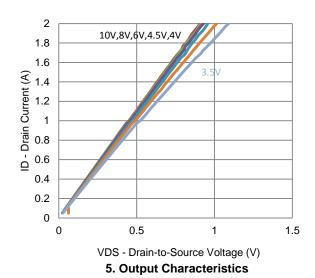
## **Typical Electrical Characteristics**



1. On-Resistance vs. Drain Current



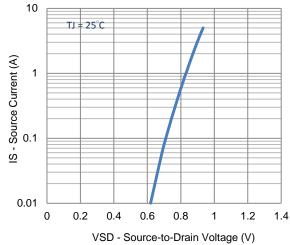
3. On-Resistance vs. Gate-to-Source Voltage



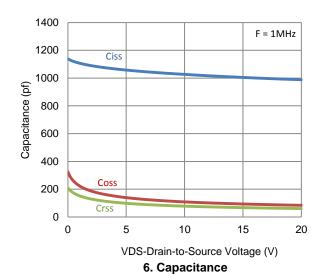
2
TJ = 25°C

1.6
(4)
tu 1.2
0
0
0
1
2
3
4
5
VGS - Gate-to-Source Voltage (V)

2. Transfer Characteristics

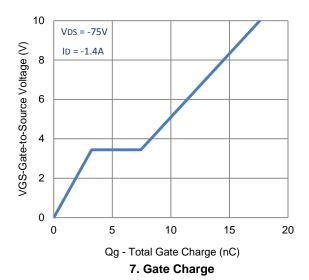


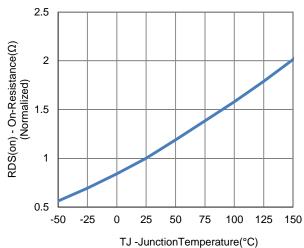
4. Drain-to-Source Forward Voltage

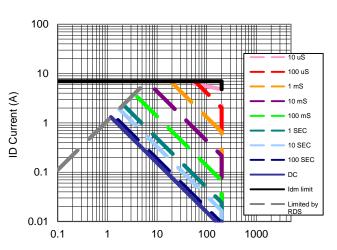


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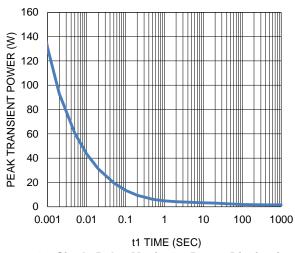
## **Typical Electrical Characteristics**







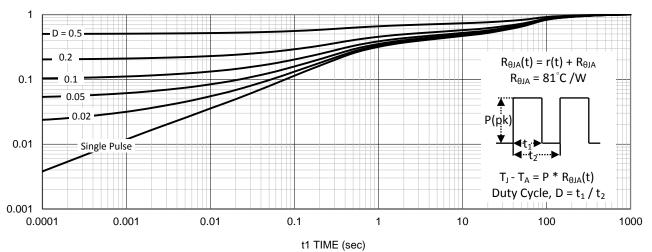
8. Normalized On-Resistance Vs Junction Temperature



VDS Drain to Source Voltage (V)

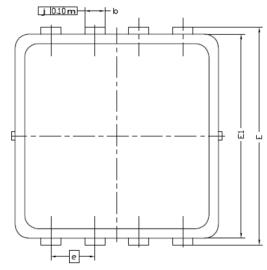
9. Safe Operating Area

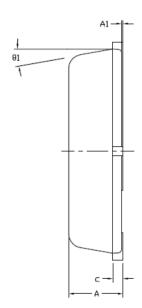
10. Single Pulse Maximum Power Dissipation

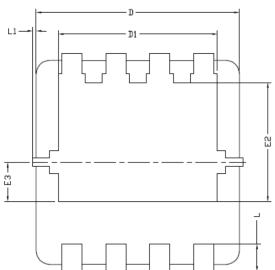


11. Normalized Thermal Transient Junction to Ambient

# Package Information







DIM,	MILLIMETERS			INCHES			
	NIM	NDM	MAX	MIN	NDM	MAX	
Α	0,700	0,80	0.900	0,0276	0,0315	0,0354	
A1	0,00		0,05	0,000		0'005	
b	0.24	0.30	0.35	0.009	0.012	0.014	
C	0.10	0.152	0,25	0.004	0.006	0.010	
D	3.00 BSC			0.118 BSC			
D1	2,35 BSC			0.093 BSC			
Е	3.20 BSC			0.126 BSC			
E1	3	3.00 B2C			0.118 BSC		
E2	1.75 BSC			0.069 BSC			
E3	0,575 BSC			0.023 BSC			
е	0	0.65 BSC			0.026 BSC		
L	0,30	0,40	0,50	0,0118	0,0157	0,0197	
L1	0		0,100	0		0,004	
91	0°	10°	12°	0°	10°	12°	